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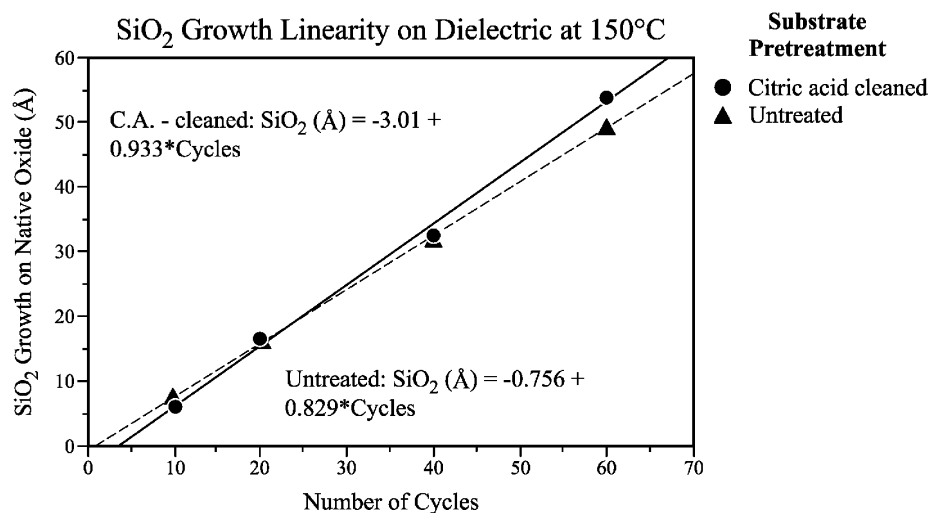


FIG. 1

(57) Abstract: A thermal atomic layer deposition method for selectively deposition of silicon and oxygen containing dielectric film selected from silicon oxide or carbon doped silicon oxide abundantly on a dielectric surface but not less on a metal surface employing a silicon precursor having at least three isocyanato ligands.

[Continued on next page]

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